

UNITED STATES PATENT AND TRADEMARK OFFICE
CERTIFICATE OF CORRECTION

PATENT NO. : 6,897,542 B2
DATED : May 24, 2005
INVENTOR(S) : Charles H. Dennison

Page 1 of 1

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

Title page.

Item [56], **References Cited**, U.S. PATENT DOCUMENTS, replace
"6,097,677 A 8/2000 Wu" with -- 6,087,677 A 7/2000 Wu --.

Column 3.

Line 26, replace "nitride (Si₃N) or silicon oxynitride (Si_xO_yN_z, wherein x, y" with
-- nitride (Si₃N₄) or silicon oxynitride (Si_xO_yN_z, wherein x, y --.

Column 6.

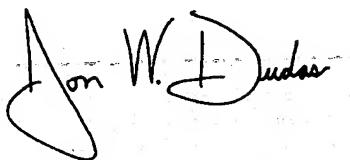
Line 36, replace "throughto the first diffusion region and having a second" with
-- through to the first diffusion region and having a second --.

Column 8.

Line 16, replace "with the planar uppermost surface. of the insulative" with
-- with the planar uppermost surface of the insulative --.

Signed and Sealed this

Fourth Day of April, 2006



JON W. DUDAS
Director of the United States Patent and Trademark Office